

L Number	Hits	Search Text	DB	Time stamp
1	7875	residue\$ near5 (measur\$4 or detect\$4 or inspect\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/10 14:47
2	3411	chemical near3 mechanical near planarization	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/10 14:47
3	5166	chemical near3 mechanical near3 planarization	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/10 14:48
4	18	(residue\$ near5 (measur\$4 or detect\$4 or inspect\$4)) and (chemical near3 mechanical near3 planarization)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/10 15:03
5	4	6137570.URPN.	USPAT	2003/06/10 14:52
6	383107	light near3 source	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/10 15:03
7	868708	detector\$	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/10 15:03
8	223	(residue\$ near5 (measur\$4 or detect\$4 or inspect\$4)) and (light near3 source) and detector\$	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/10 15:04
9	32071	spectrophotometer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/10 15:04
10	25	((residue\$ near5 (measur\$4 or detect\$4 or inspect\$4)) and (light near3 source) and detector\$) and spectrophotometer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/10 15:46
11	223	(residue\$ near5 (measur\$4 or detect\$4 or inspect\$4)) and (light near3 source) and detector\$	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/10 15:46
12	74755	356/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/10 15:46
13	36	((residue\$ near5 (measur\$4 or detect\$4 or inspect\$4)) and (light near3 source) and detector\$) and 356/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/10 15:47
14	34	((((residue\$ near5 (measur\$4 or detect\$4 or inspect\$4)) and (light near3 source) and detector\$) and 356/\$.ccls.) not (((residue\$ near5 (measur\$4 or detect\$4 or inspect\$4)) and (light near3 source) and detector\$) and spectrophotometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/10 15:47

US-PAT-NO: 6137570

DOCUMENT-IDENTIFIER: US 6137570 A

TITLE: System and method for
analyzing topological features on
a surface

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Brief Summary Text - BSTX (5):

These and similar problems often arise when processing equipment malfunctions or degrades in performance over time. Examples of such equipment include plasma etchers, deposition systems, chemical mechanical planarization systems, reticle processing, and photolithography equipment. Obviously, a manufacturer needs to know when the process equipment ceases to function in an acceptable manner.

Detailed Description Text - DETX (8):

For the case of an opening in a surface or surface film, this invention may evaluate various parameters characterizing such openings. For example, the invention may detect variations in opening diameter, depth, and angle. Thus, it may detect whether a via or contact is

over etched, under etched, too wide,
too narrow, too conical, angled too far from
the surface normal, etc. It may
also detect the presence of residue left in
such openings.